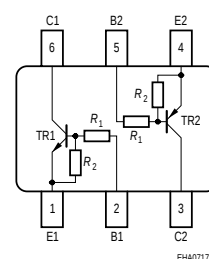
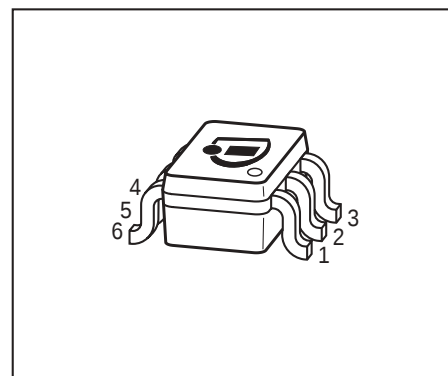


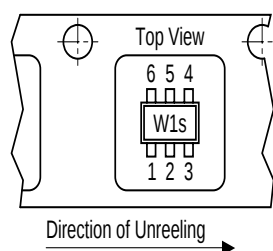
NPN/PNP Silicon Digital Transistor Array

- Switching circuit, inverter, interface circuit, driver circuit
- Two (galvanic) internal isolated NPN/PNP Transistors in one package
- Built in bias resistor NPN and PNP ($R_1=10\text{ k}\Omega$, $R_2=47\text{ k}\Omega$)
- Pb-free (ROHS compliant) package¹⁾
- Qualified according AEC Q101



EHA07176

Tape loading orientation



Marking on SOT-363 package
(for example W1s)
corresponds to pin 1 of device

Position in tape: pin 1
opposite of feed hole side

EHA07193

Type	Marking	Pin Configuration						Package
BCR35PN	WUs	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SOT363

Maximum Ratings for NPN and PNP Types

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	50	V
Collector-base voltage	V_{CBO}	50	
Input forward voltage	$V_{i(fwd)}$	40	
Input reverse voltage	$V_{i(rev)}$	6	
DC collector current	I_C	100	mA
Total power dissipation, $T_S = 115\text{ }^{\circ}\text{C}$	P_{tot}	250	mW
Junction temperature	T_j	150	$^{\circ}\text{C}$
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Junction - soldering point ²⁾	R_{thJS}	≤ 140	K/W
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¹Pb-contain package may be available upon special request

²For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics at $T_A=25^{\circ}\text{C}$, unless otherwise specified

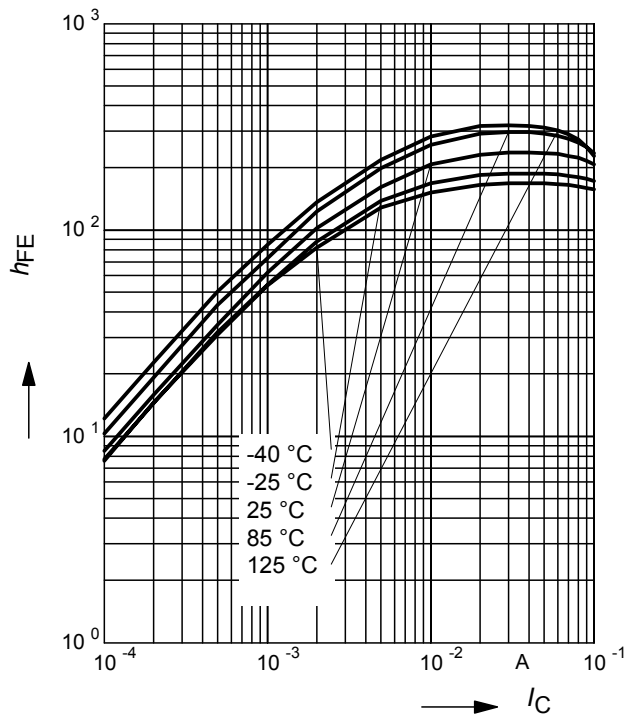
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics for NPN and PNP Types					
Collector-emitter breakdown voltage $I_C = 100\text{ }\mu\text{A}$, $I_B = 0$	$V_{(BR)CEO}$	50	-	-	V
Collector-base breakdown voltage $I_C = 10\text{ }\mu\text{A}$, $I_E = 0$	$V_{(BR)CBO}$	50	-	-	
Collector cutoff current $V_{CB} = 40\text{ V}$, $I_E = 0$	I_{CBO}	-	-	100	nA
Emitter cutoff current $V_{EB} = 6\text{ V}$, $I_C = 0$	I_{EBO}	-	-	167	μA
DC current gain 1) $I_C = 5\text{ mA}$, $V_{CE} = 5\text{ V}$	h_{FE}	70	-	-	-
Collector-emitter saturation voltage1) $I_C = 10\text{ mA}$, $I_B = 0.5\text{ mA}$	V_{CEsat}	-	-	0.3	V
Input off voltage $I_C = 100\text{ }\mu\text{A}$, $V_{CE} = 5\text{ V}$	$V_{i(off)}$	0.5	-	1	
Input on Voltage $I_C = 2\text{ mA}$, $V_{CE} = 0.3\text{ V}$	$V_{i(on)}$	0.5	-	1.4	
Input resistor	R_1	7	10	13	k Ω
Resistor ratio	R_1/R_2	0.19	0.21	0.24	-
AC Characteristics for NPN and PNP Types					
Transition frequency $I_C = 10\text{ mA}$, $V_{CE} = 5\text{ V}$, $f = 100\text{ MHz}$	f_T	-	150	-	MHz
Collector-base capacitance $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{cb}	-	2	-	pF

1) Pulse test: $t < 300\mu\text{s}$; $D < 2\%$

NPN Type

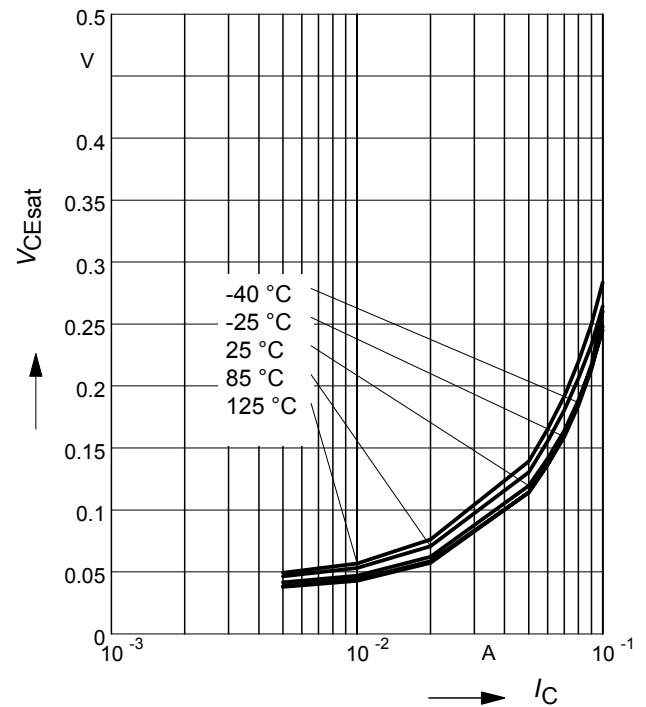
DC Current Gain $h_{FE} = f(I_C)$

$V_{CE} = 5V$ (common emitter configuration)



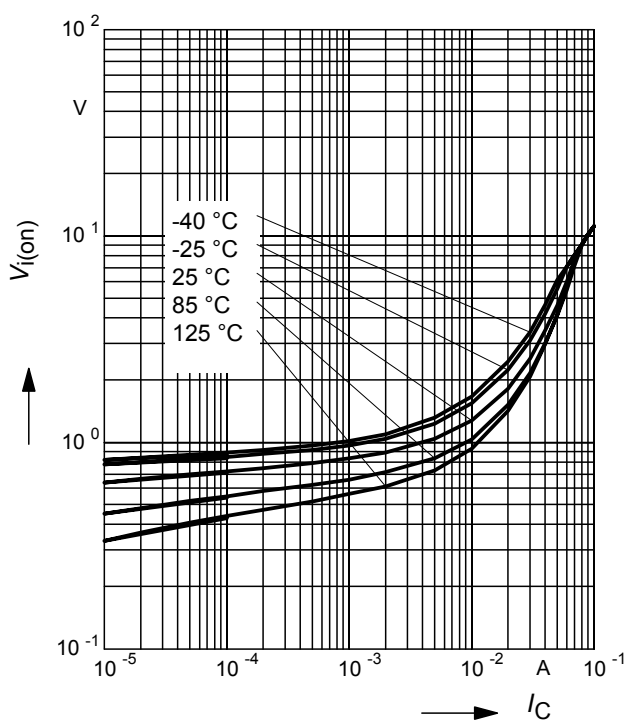
Collector-Emitter Saturation Voltage

$V_{CEsat} = f(I_C), h_{FE} = 20$



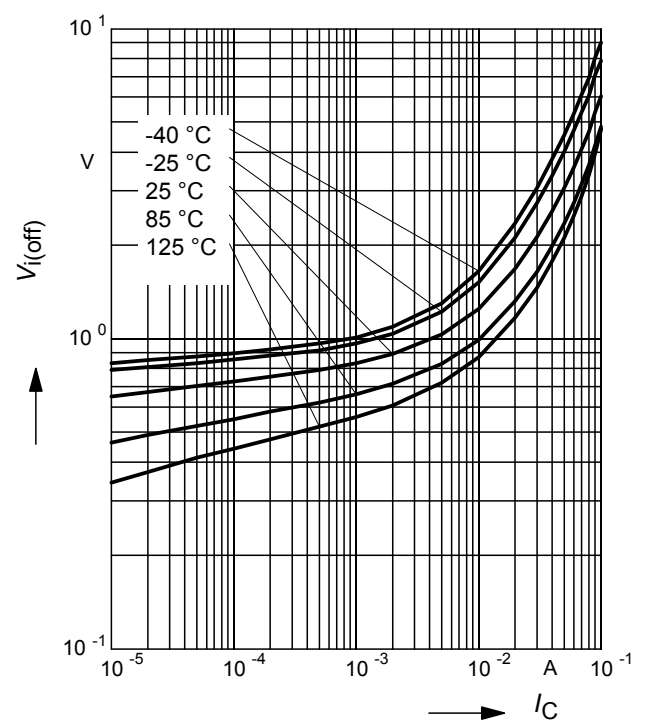
Input on Voltage $V_{i(on)} = f(I_C)$

$V_{CE} = 0.3V$ (common emitter configuration)



Input off voltage $V_{i(off)} = f(I_C)$

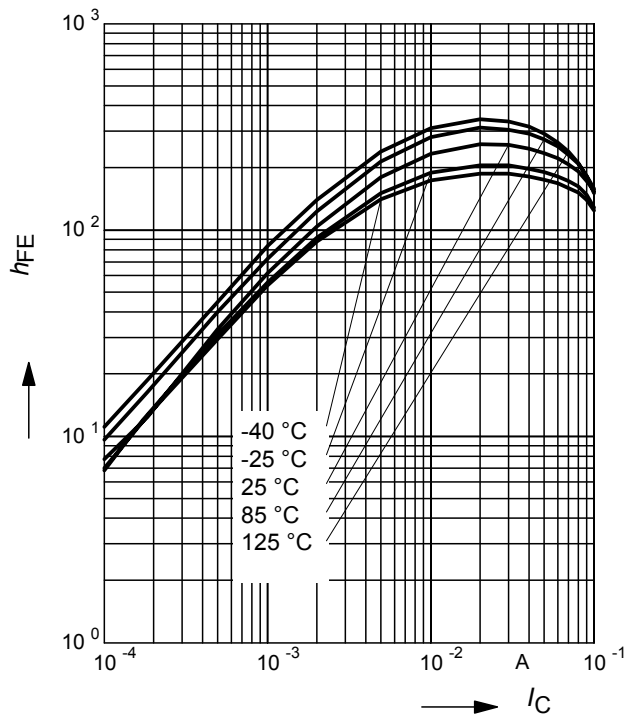
$V_{CE} = 5V$ (common emitter configuration)



PNP Type

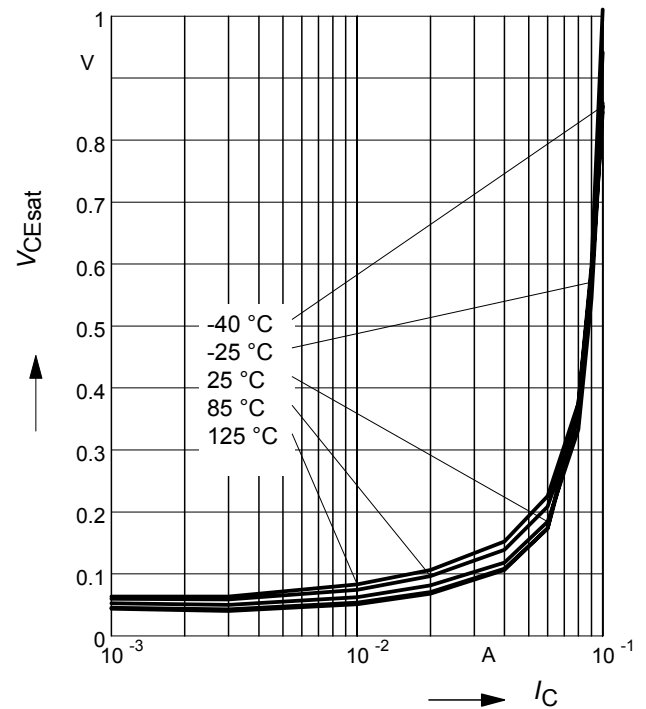
DC Current Gain $h_{FE} = f(I_C)$

$V_{CE} = 5V$ (common emitter configuration)



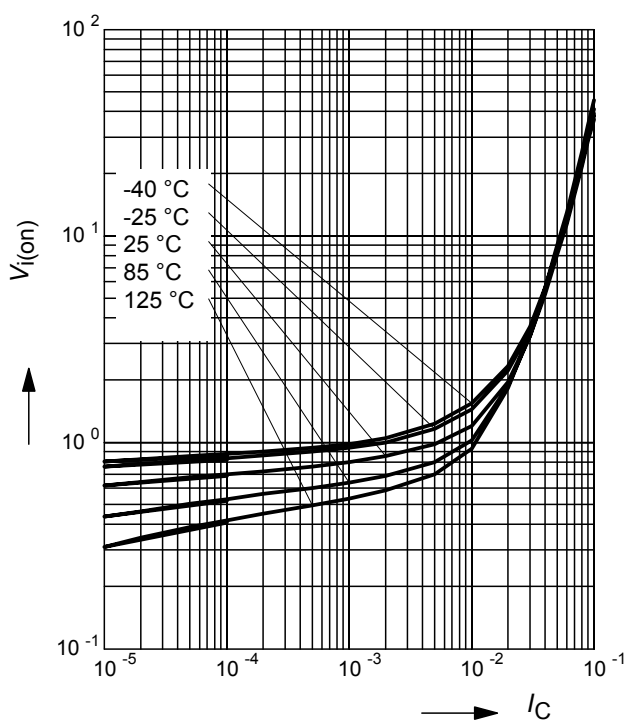
Collector-Emitter Saturation Voltage

$V_{CEsat} = f(I_C), h_{FE} = 20$



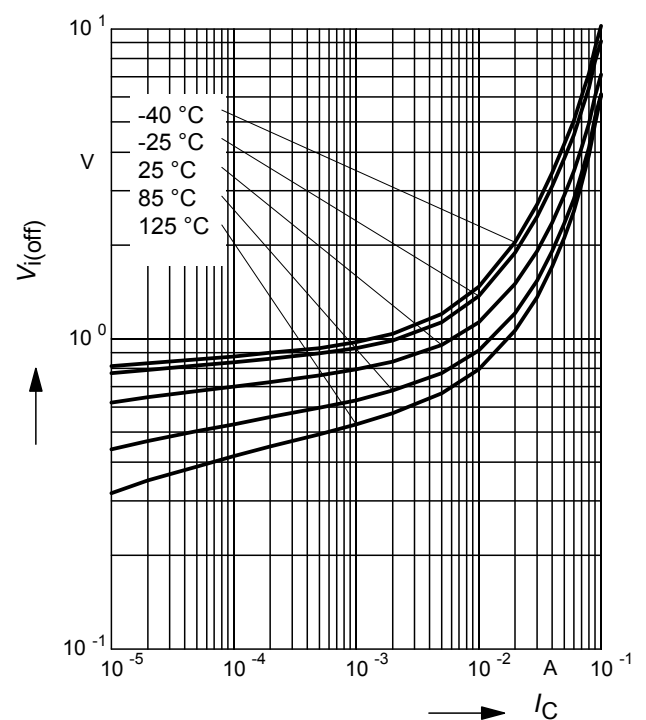
Input on Voltage $V_{i(on)} = f(I_C)$

$V_{CE} = 0.3V$ (common emitter configuration)

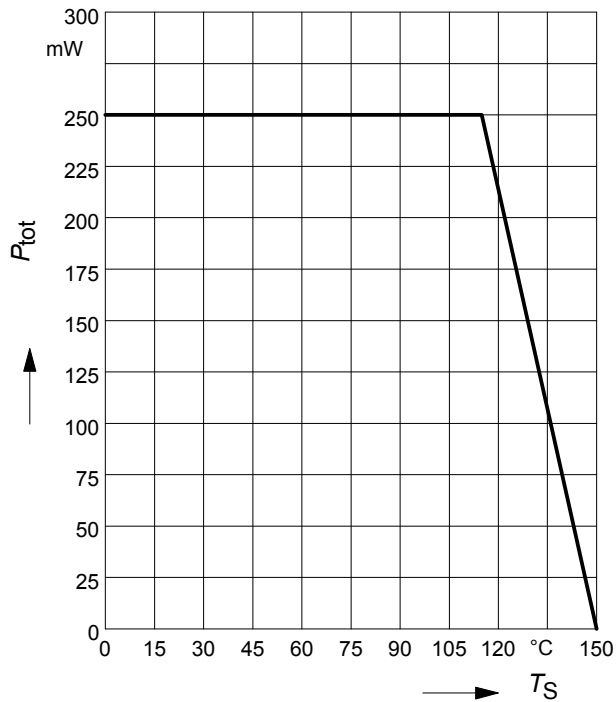


Input off voltage $V_{i(off)} = f(I_C)$

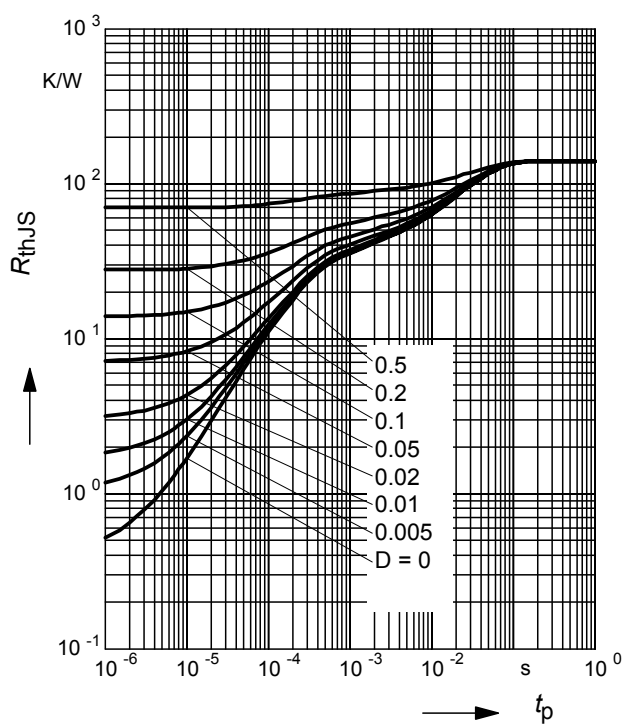
$V_{CE} = 5V$ (common emitter configuration)



Total power dissipation $P_{\text{tot}} = f(T_S)$



Permissible Pulse Load $R_{\text{thJS}} = f(t_p)$



Permissible Pulse Load

$P_{\text{totmax}} / P_{\text{totDC}} = f(t_p)$

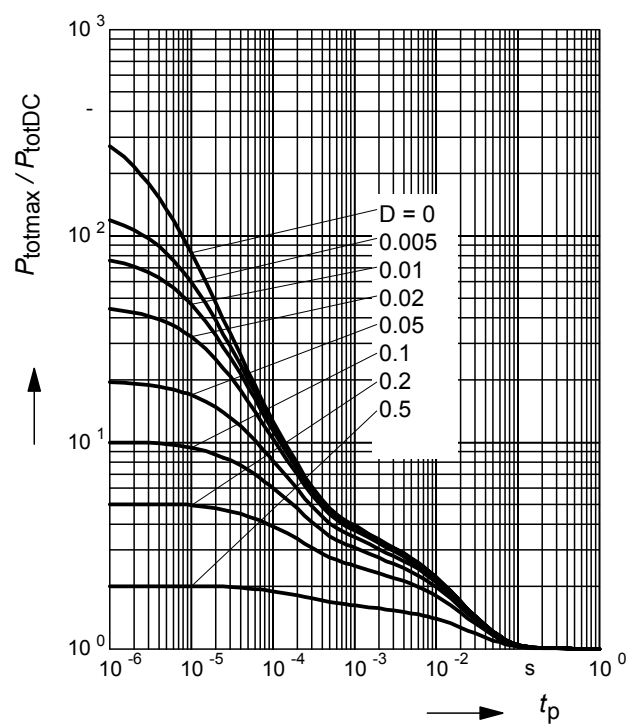


Diagram illustrating the marking on the BCR108S component:

- Manufacturer:** Infineon Technologies
- Date code (Year/Month):** 06 55 (2005, June)
- Pin 1 marking:** Indicated by a circle at the bottom left corner.
- Laser marking:** The entire marking 'WH S 06 55'.
- Type code:** BCR108S

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